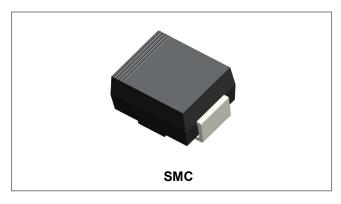






## **30BQ100 SCHOTTKY RECTIFIER**



### **Features**

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



#### **Applications**

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	100	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>C</sub> =148°C, rectangular wave form	3.0	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse, T <sub>C</sub> =25°C	80	Α

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 3 A, Pulse, T <sub>J</sub> = 25 °C	0.76	0.79	V
		@ 6 A, Pulse, T <sub>J</sub> = 25 °C	-	0.90	V
	$V_{F2}$	@ 3 A, Pulse, T <sub>J</sub> = 125 °C	0.60	0.62	V
		@ 6 A, Pulse, T <sub>J</sub> = 125°C	-	0.70	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = Rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 25 °C	0.0001	0.5	mA
	I <sub>R2</sub>	@V <sub>R</sub> = Rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 100 °C	0.04	5	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	80	115	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	3.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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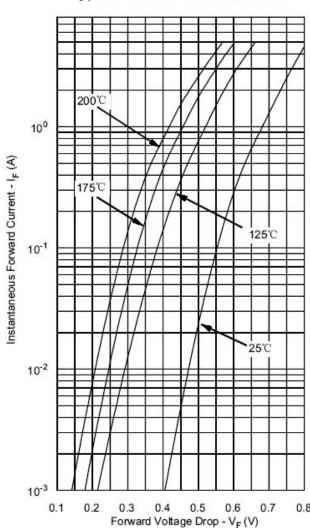


### **Thermal-Mechanical Specifications:**

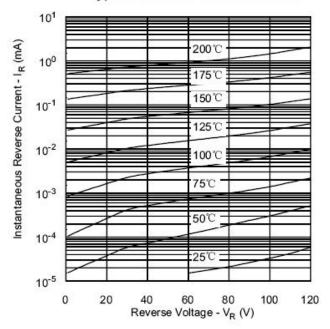
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Lead	R <sub>θJL</sub>	-	12	°C/W
Typical Thermal Resistance Junction to Case	$R_{ heta JA}$	DC operation	46	°C/W
Approximate Weight	wt	-	0.21	g
Case Style	SMC			

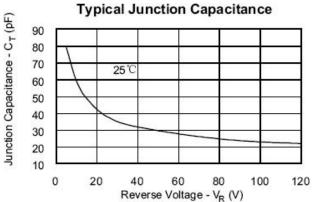
# **Ratings and Characteristics Curves**

### Typical Forward Characteristics



### Typical Reverse Characteristics





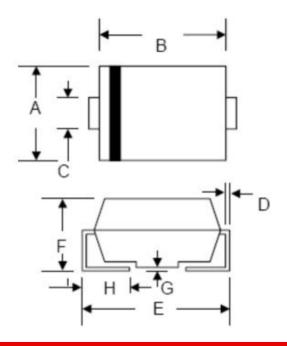
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### **Mechanical Dimensions SMC**



OVMBOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	5.59	6.22	0.220	0.245	
В	6.60	7.11	0.260	0.280	
С	2.75	3.25	0.108	0.128	
D	0.152	0.305	0.006	0.012	
Е	7.75	8.25	0.305	0.325	
F	2.00	2.95	0.079	0.116	
G	0.051	0.203	0.002	0.008	
Н	0.76	1.60	0.030	0.063	

### **Ordering Information**

Device	Package	Shipping
30BQ100	SMC (Pb-Free)	3000pcs / reel
30BQ100TR	SMC (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### **Marking Diagram**

Where XXXXX is YYWWL



 SC3J
 = Part Name

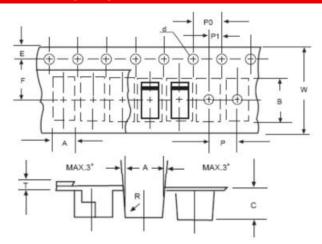
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

# **Carrier Tape Specification SMC**



SYMBOL	Millimeters		
	Min.	Max.	
Α	5.90	6.10	
В	8.20	8.40	
С	2.40	2.60	
d	1.40	1.60	
Е	1.40	1.60	
F	7.60	7.70	
Р	7.90	8.10	
P0	3.90	4.10	
P1	3.90	4.10	
Т	-	0.600	
W	15.80	16.20	

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